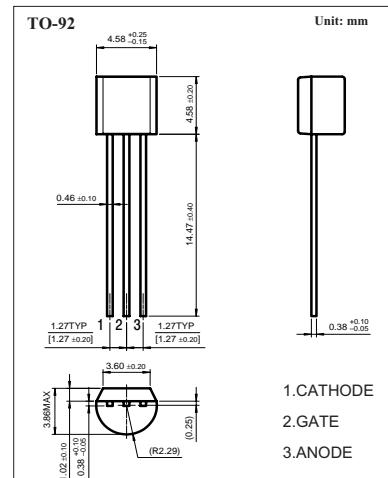
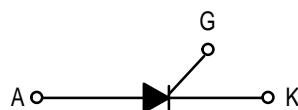


Silicon Controlled Rectifiers

MCR100-8

■ Features

- Blocking voltage to 600V
- RMS on-state current to 0.8 A
- General purpose switching



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Peak Repetitive Forward and Reverse Blocking Voltage (TJ = 25 to 125°C, RGK = 1 K Ω)	VDRM and VRMM	600	V
Forward Current RMS	IT(RMS)	0.8	A
Peak Forward Surge Current, TA = 25°C (1/2 Cycle, Sine Wave, 60 Hz)	ITSM	10	A
Circuit Fusing Considerations (t = 8.3 ms)	I ² t	0.415	A ² s
Peak Gate Power — Forward, TA = 25°C	PGM	0.1	W
Average Gate Power — Forward, TA = 25°C	PGF(AV)	0.01	W
Peak Gate Current — Forward, TA = 25°C (300 ms, 120 PPS)	IGFM	1	A
Peak Gate Voltage — Reverse	VGRM	5	V
Thermal Resistance, Junction to Ambient	R _{θ JA}	200	°C/W
Thermal Resistance, Junction to Case	R _{θ JC}	75	°C/W
Operating Junction Temperature Range @ Rated VRMM and VDRM	T _J	-40 to +125	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C
Lead Solder Temperature(<1/16"from case, 10 s max)		230	°C

MCR100-8

■ Electrical Characteristics ($T_a = 25^\circ\text{C}$, $R_{GK} = 1 \text{ k}\Omega$ unless otherwise noted.)

Parameter	Symbol	Testconditons	Min	Max	Unit
Peak Forward or Reverse Blocking Current	I_{DRM}, I_{RRM}	$V_{AK} = \text{Rated } V_{DRM} \text{ or } V_{RRM}$		10 100	$\mu\text{ A}$
Forward "On" Voltage *1	V_{TM}	$I_{TM} = 1 \text{ A Peak @ } T_a = 25^\circ\text{C}$		1.7	V
Gate Trigger Current (Continuous DC) *2	I_{GT}	Anode Voltage = 7 V, $R_L = 100\Omega$		200	$\mu\text{ A}$
Gate Trigger Voltage (Continuous DC)	V_{GT}	Anode Voltage=7V, $R_L=100\Omega$ Anode Voltage = Rated $V_{DRM}, R_L=100\Omega$		0.8 1.2	V
Holding Current	I_H	Anode Voltage=7V,initiating current=20mA		5 10	mA

*1. Forward current applied for 1 ms maximum duration, duty cycle $\leq 1\%$.

*2. R_{GK} current is not included in measurement.

■ Marking

Marking	MCR100-8
---------	----------